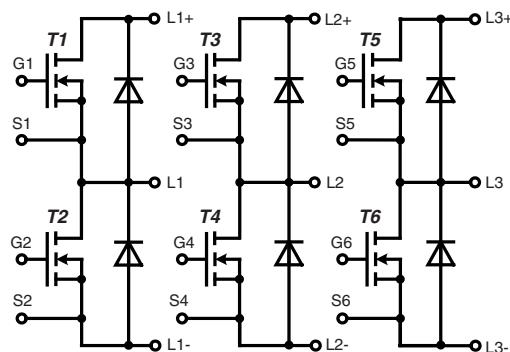
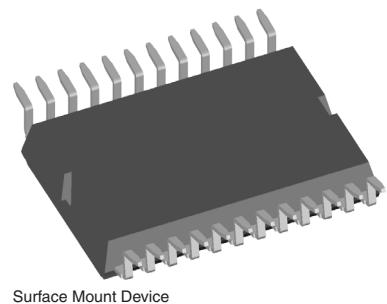


Three phase full Bridge
with Trench MOSFETs
in DCB isolated high current package

V_{DSS} = 75 V
 I_{D25} = 255 A
 $R_{DSon\ typ.}$ = 1.1 mΩ

Part number
MTI200WX75GD



Features / Advantages:

- MOSFETs in trench technology:
 - low R_{DSon}
 - optimized intrinsic reverse diode
- package:
 - high level of integration
 - high current capability
 - aux. terminals for MOSFET gate control
 - terminals for soldering or welding connections
 - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings
- High current capability

Applications:

- AC drives
 - in automobiles
 - electric power steering
 - starter generator
 - in industrial vehicles
 - propulsion drives
 - fork lift drives
 - Battery supplied equipment
 - DC-DC converter

Package: ISOPLUS-DIL®

- High level of integration
- RoHS compliant
- Terminals for soldering or welding connections
- Space and weight savings
- High reliability
- Low thermal impedance

Terms & Conditions of usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;
- the conclusion of quality agreements;
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, test conditions and dimensions.

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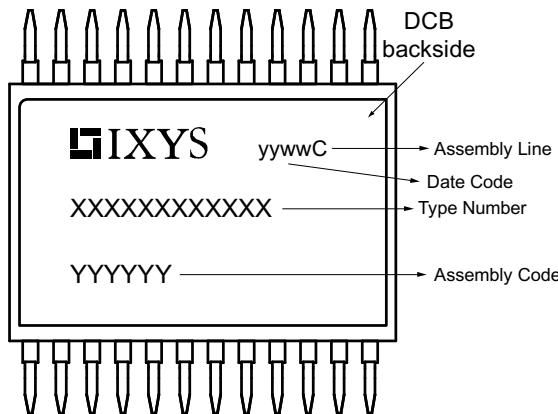
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1 - 7

MOSFETs			Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{DSS}	drain source breakdown voltage	$T_{VJ} = 25^\circ\text{C}$ to 150°C			75	V
V_{GS}	max. DC gate source voltage				± 15	V
V_{GSM}	max. transient gate source voltage				± 20	V
I_{D25}	continuous drain current	$T_C = 25^\circ\text{C}$			255	A
I_{D90}	(die capability)	$T_C = 90^\circ\text{C}$			190	A
$R_{DS(on)}$ ¹⁾	static drain source on resistance	on chip level at $I_D = 100 \mu\text{A}$; $V_{GS} = 10 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	1.1 1.8	1.3	$\text{m}\Omega$ $\text{m}\Omega$
$V_{GS(th)}$	gate threshold voltage	$I_D = 275 \mu\text{A}$; $V_{DS} = V_{GS}$	$T_{VJ} = 25^\circ\text{C}$	2.3	3.1	3.8
I_{DSS}	drain source leakage current	$V_{DS} = V_{DSS}$; $V_{GS} = 0 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		10	$100 \mu\text{A}$
I_{GSS}	gate source leakage current	$V_{GS} = \pm 20 \text{ V}$; $V_{DS} = 0 \text{ V}$			500	nA
R_G	gate resistance	on chip			2.7	Ω
C_{iss}	input capacitance	$V_{GS} = 0 \text{ V}$; $V_{DS} = 38 \text{ V}$; $f = 1 \text{ Mhz}$			10.8	nF
C_{oss}	output capacitance				2.42	nF
C_{rss}	reverse transfer capacitance				110	-
Q_g	total gate charge	$V_{GS} = 10 \text{ V}$; $V_{DS} = 38 \text{ V}$; $I_D = 100 \text{ A}$			155	nC
Q_{gs}	gate source charge				53	nC
Q_{gd}	gate drain (Miller) charge				32	nC
$t_{d(on)}$	turn-on delay time	$T_{VJ} = 125^\circ\text{C}$			145	ns
t_r	current rise time				70	ns
$t_{d(off)}$	turn-off delay time				520	ns
t_f	current fall time				55	ns
E_{on}	turn-on energy per pulse				80	μJ
E_{off}	turn-off energy per pulse				350	μJ
$E_{rec(off)}$	turn-off reverse recovery losses				8	μJ
R_{thJC}	thermal resistance junction to case				0.85	K/W
R_{thJH}	thermal resistance junction to heatsink	with heat transfer paste (IXYS test setup)			1.1	K/W
¹⁾ $V_{DS} = I_D \cdot (R_{DS(on)} + 2 \cdot R_{\text{Pin to Chip}})$						
Source-Drain Diode						
I_{F25}	forward current (body diode)	$V_{GS} = 0 \text{ V}$	$T_C = 25^\circ\text{C}$		175	A
I_{F90}			$T_C = 90^\circ\text{C}$		100	A
V_{SD}	source drain voltage	$I_F = 100 \text{ A}$; $V_{GS} = 0 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	0.9	1.2	V
Q_{RM}	reverse recovery charge	$V_R = 30 \text{ V}$; $I_F = 100 \text{ A}$	$T_{VJ} = 125^\circ\text{C}$		730	nC
I_{RM}	max. reverse recovery current				27	A
t_{rr}	reverse recovery time	$R_G = 27 \Omega$			42	ns

Package ISOPLUS-DIL®

Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	<i>RMS current</i>	per pin in main current paths (L1+...L3+, L1-...L3-, L1...L3) may be additionally limited by external connections (PCB tracks) 2 pins for output L1, L2, L3			75	A
T_{stg}	<i>storage temperature</i>		-55	125		°C
T_{op}	<i>operation temperature</i>		-55	150		°C
T_{vj}	<i>virtual junction temperature</i>		-55	175		°C
Weight				13		g
F_c	<i>mounting force with clip</i>		50	250		N
V_{ISOL}	<i>isolation voltage</i>	$t = 1 \text{ second}$ $t = 1 \text{ minute}$	50/60 Hz, RMS, $I_{ISOL} \leq 1 \text{ mA}$	1200		V
				1000		V
$R_{\text{pin-chip}}$	<i>resistance terminal to chip</i>	$V_{DS} = I_D \cdot (R_{DS(on)} + 2 \cdot R_{\text{pin to chip}})$		0.5		mΩ
C_p	<i>coupling capacity</i>	between shorted pins and back side metallization		160		pF

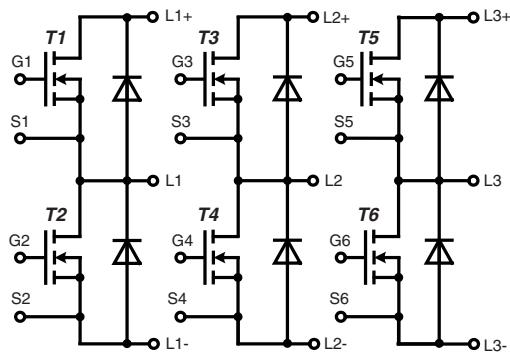
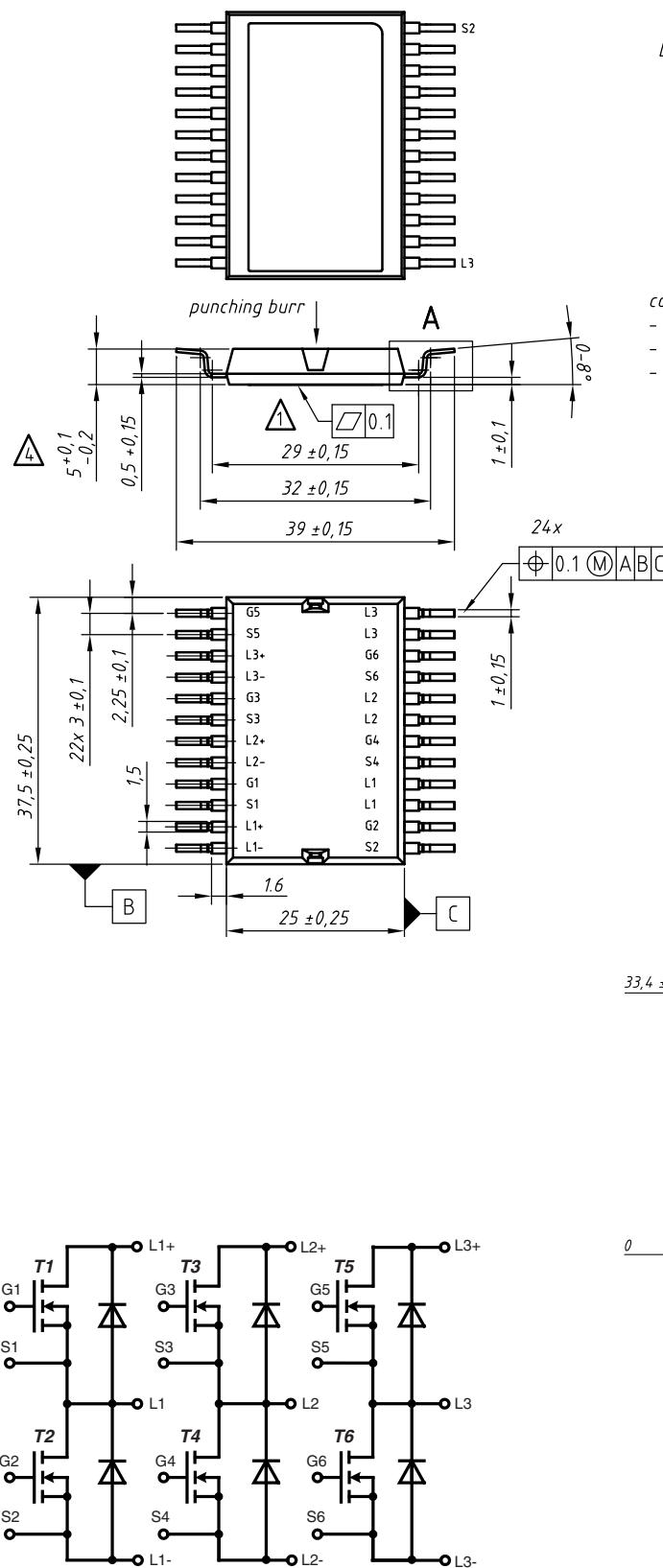


Part number

M = MOSFET
 T = Trench
 I = Infineon Trench
 200 = Current Rating [A]
 WX = 6-Pack with separated phase legs
 75 = Reverse Voltage [V]
 GD = ISOPLUS-DIL

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MTI200WX75GD-SMD	MTI200WX75GD	Tube	13	516955

Outlines ISOPLUS-DIL®



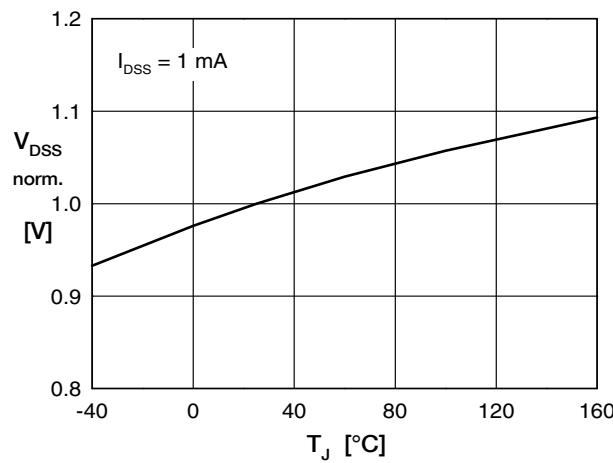


Fig.1 Drain source breakdown voltage V_{DSS} vs. junction temperature T_{VJ}

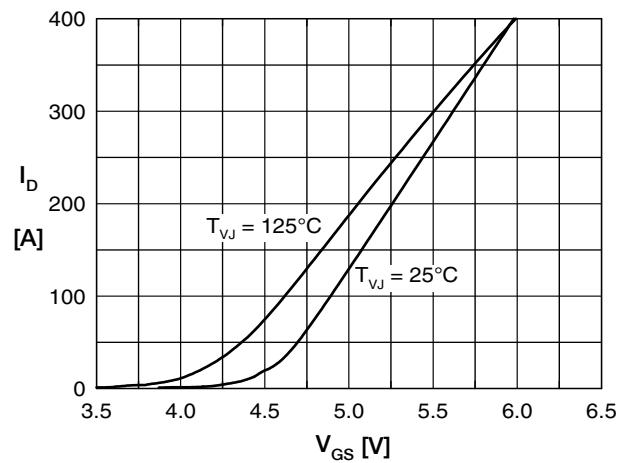


Fig. 2 Typ. transfer characteristics

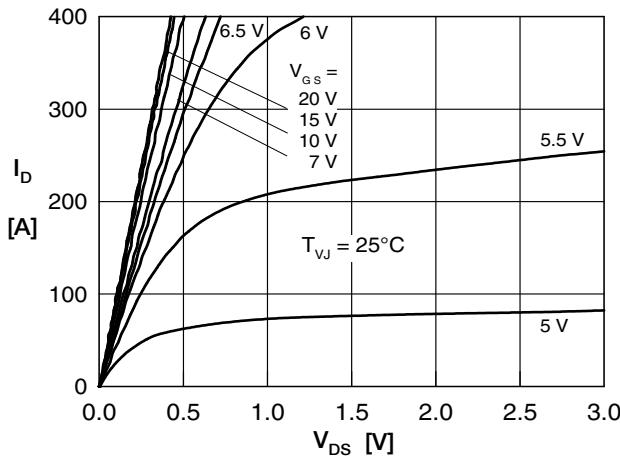


Fig. 3 Typ. output characteristics on die level

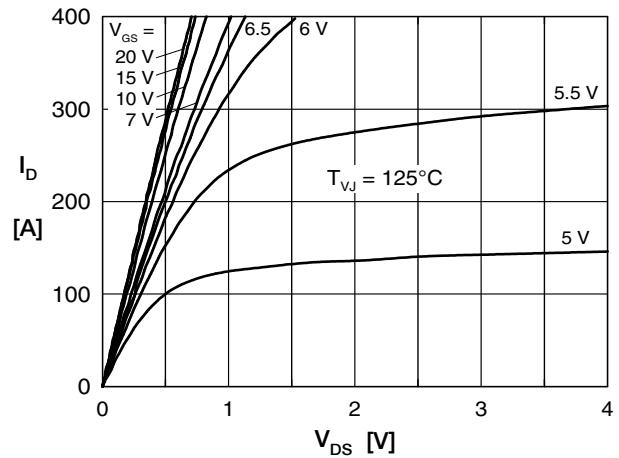


Fig. 4 Typ. output characteristics on die level

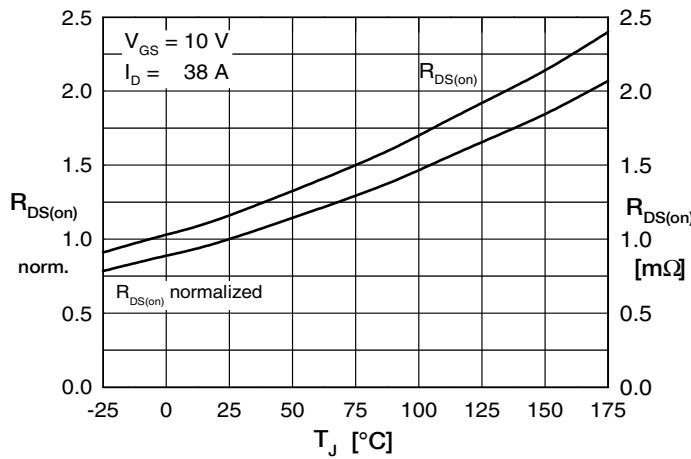


Fig.5 Drain source on-state resistance $R_{DS(on)}$ vs. junction temperature $T_{V,I}$, on die level

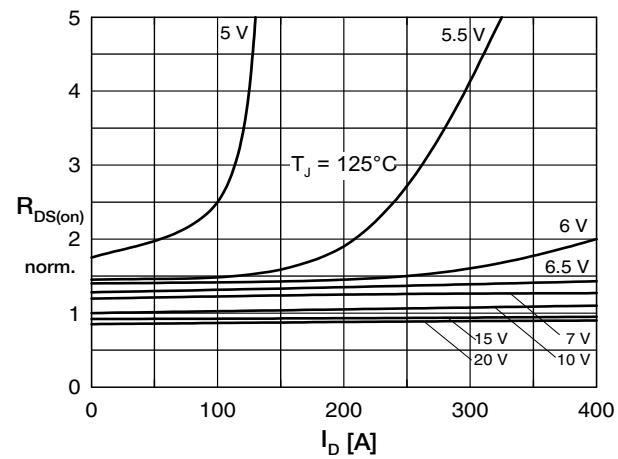


Fig. 6 Drain source on-state resistance $R_{DS(on)}$ versus I_D , on die level

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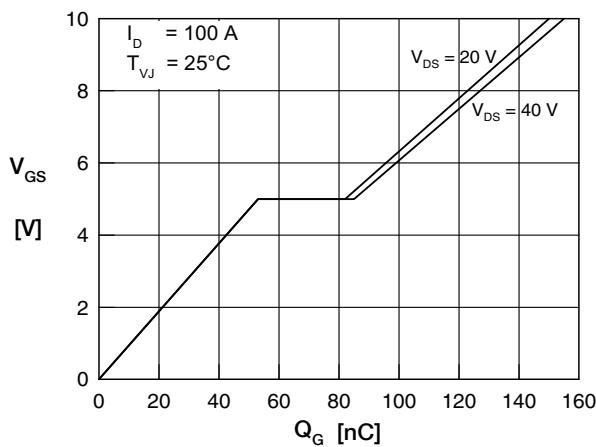


Fig. 7 Typical turn on gate charge

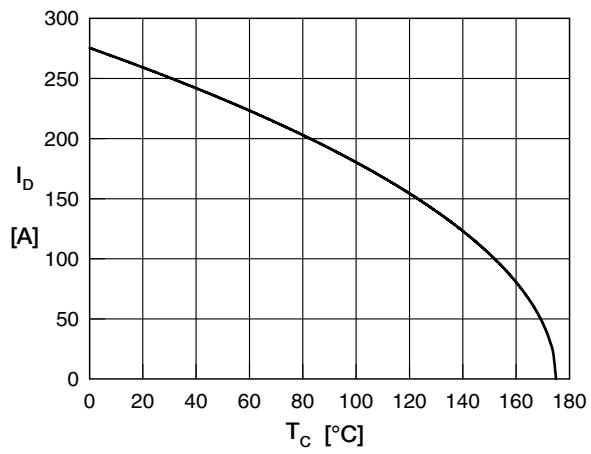
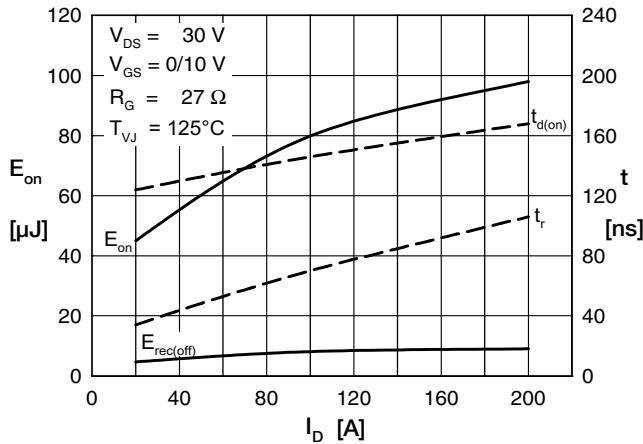
Fig. 8 Drain current I_D vs. case temperature T_C (Chip capability)

Fig. 9 Typ. turn-on energy and switching times versus drain current, inductive switching

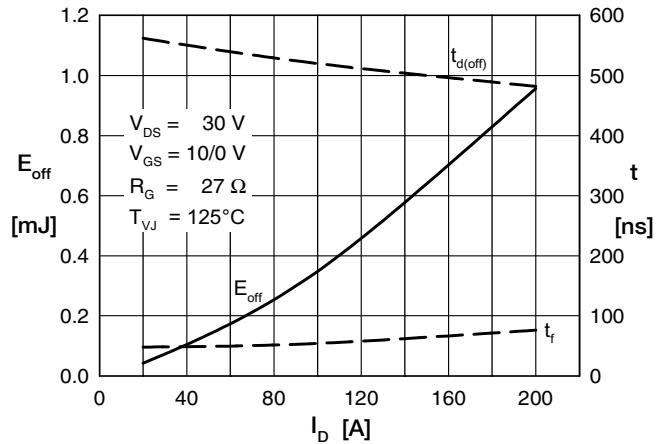


Fig. 10 Typ. turn-off energy and switching times versus drain-current, inductive switching

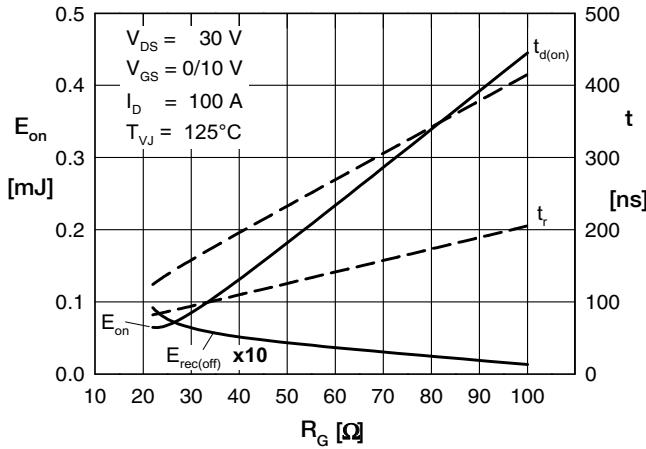


Fig. 11 Typ. turn-on energy and switching times versus gate resistor, inductive switching

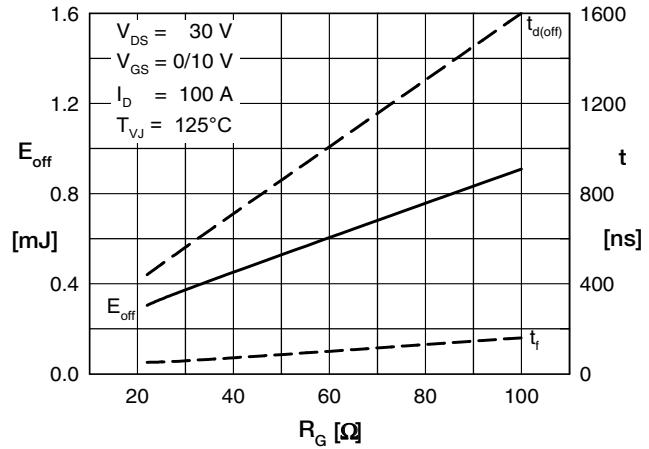


Fig. 12 Typ. turn-off energy and switching times versus gate resistor, inductive switching

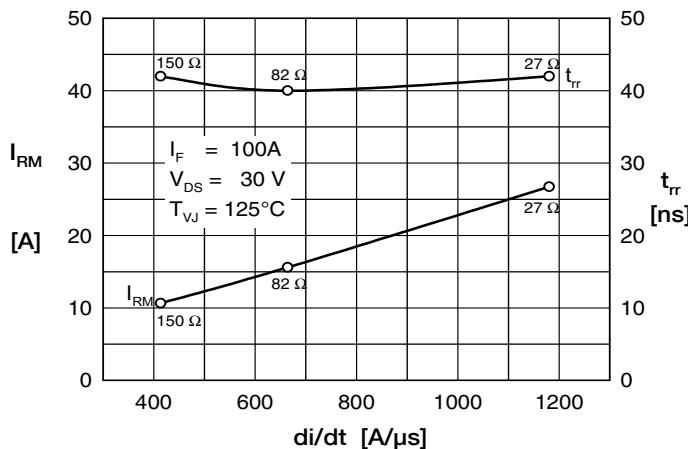


Fig. 13 Typ. reverse recovery characteristics

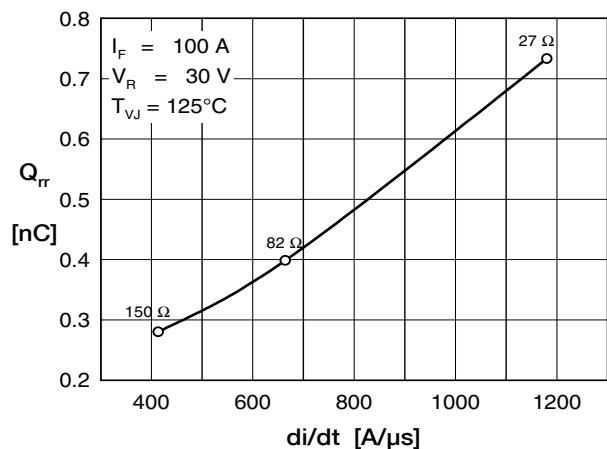


Fig. 14 Typ. reverse recovery characteristics

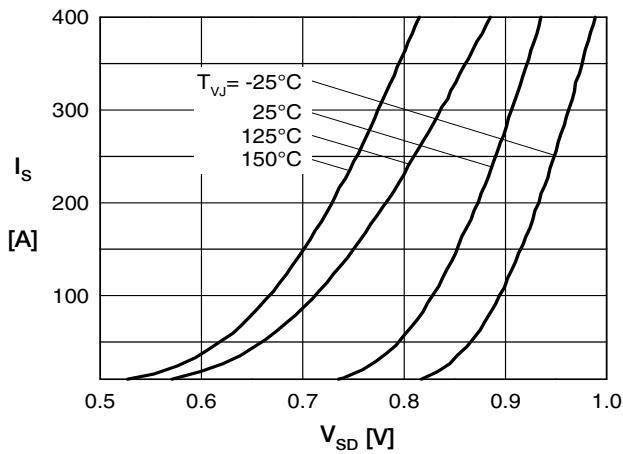
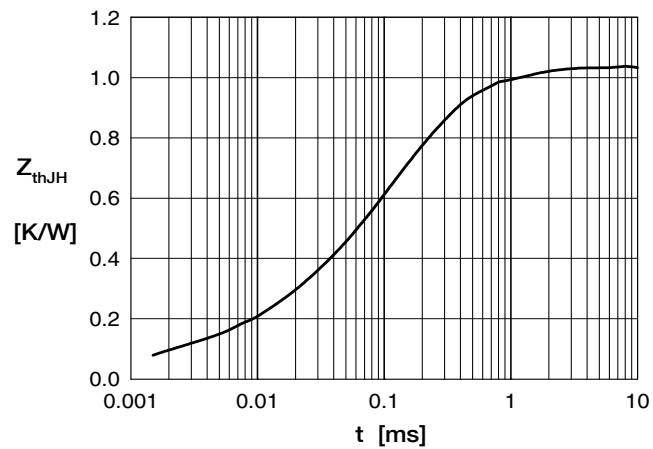
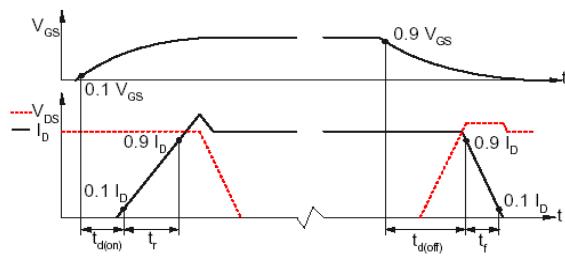
Fig. 15 Source current I_S vs. source drain voltage V_{SD} (body diode) on die levelFig. 16 Typ. thermal impedance junction to heatsink Z_{thJH} with heat transfer paste (IXYS test setup)

Fig. 17 Definition of switching times